
2SC5141

Silicon NPN Epitaxial

HITACHI

ADE-208-228A (Z)
2nd. Edition
Mar. 2001

Application

VHF / UHF wide band amplifier

Features

- High gain bandwidth product
 $f_T = 5.8$ GHz typ
- High gain, low noise figure
PG = 13 dB typ, NF = 1.6 dB typ at $f = 900$ MHz

Outline

SMPAK



1. Emitter
2. Base
3. Collector

Note: Marking is "YN-".

Attention: This device is very sensitive to electro static discharge.

It is recommended to adopt appropriate cautions when handling this transistor.

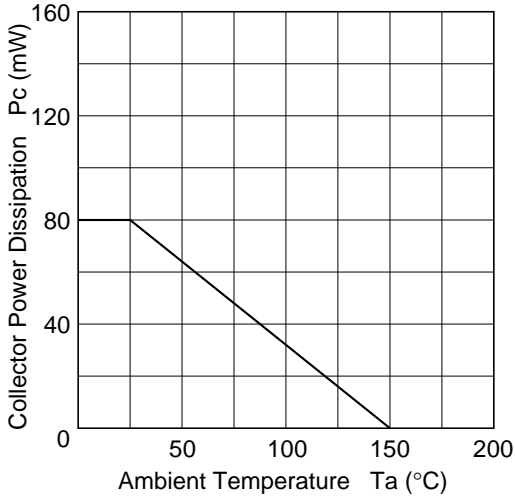
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	20	V
Collector to emitter voltage	V_{CEO}	12	V
Emitter to base voltage	V_{EBO}	2	V
Collector current	I_{C}	50	mA
Collector power dissipation	P_{C}	80	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

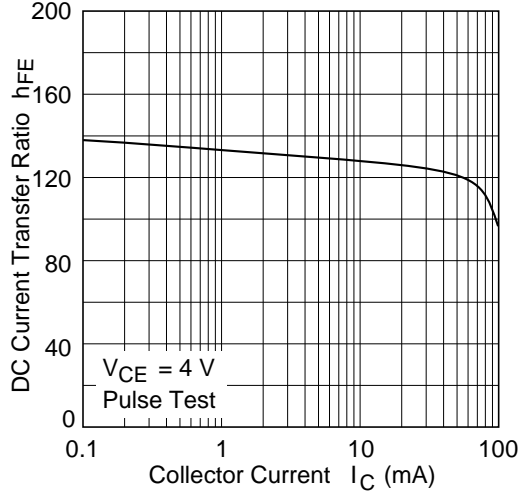
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	20	—	—	V	$I_{\text{C}} = 10 \mu\text{A}$, $I_{\text{E}} = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{\text{CB}} = 15 \text{ V}$, $I_{\text{E}} = 0$
	I_{CEO}	—	—	1	mA	$V_{\text{CE}} = 12 \text{ V}$, $R_{\text{BE}} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{\text{EB}} = 2 \text{ V}$, $I_{\text{C}} = 0$
DC current transfer ratio	h_{FE}	50	120	250		$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 20 \text{ mA}$
Collector output capacitance	C_{ob}	—	0.8	1.4	pF	$V_{\text{CB}} = 5 \text{ V}$, $I_{\text{E}} = 0$, $f = 1 \text{ MHz}$
Gain bandwidth product	f_{T}	4.0	5.8	—	GHz	$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 20 \text{ mA}$
Power gain	PG	9.5	13.0	—	dB	$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 20 \text{ mA}$, $f = 900 \text{ MHz}$
Noise figure	NF	—	1.6	3.0	dB	$V_{\text{CE}} = 4 \text{ V}$, $I_{\text{C}} = 5 \text{ mA}$, $f = 900 \text{ MHz}$

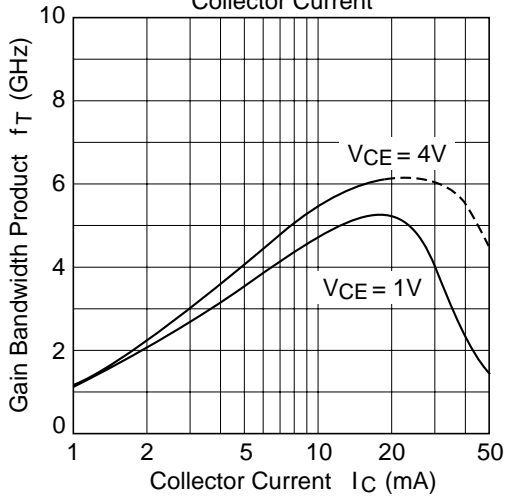
Maximum Collector Dissipation Curve



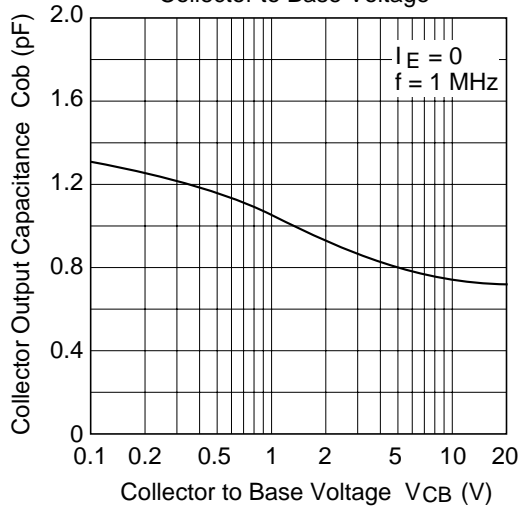
DC Current Transfer Ratio vs. Collector Current

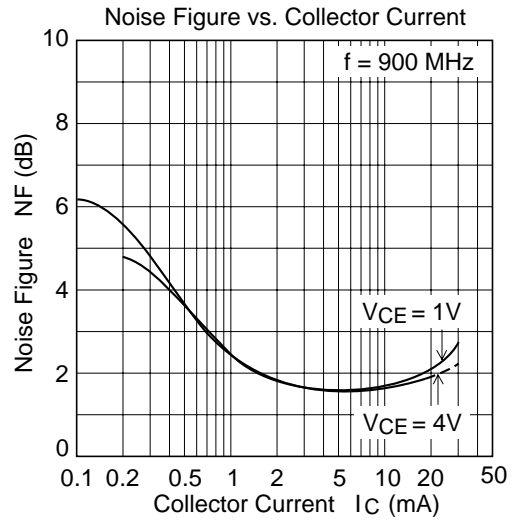
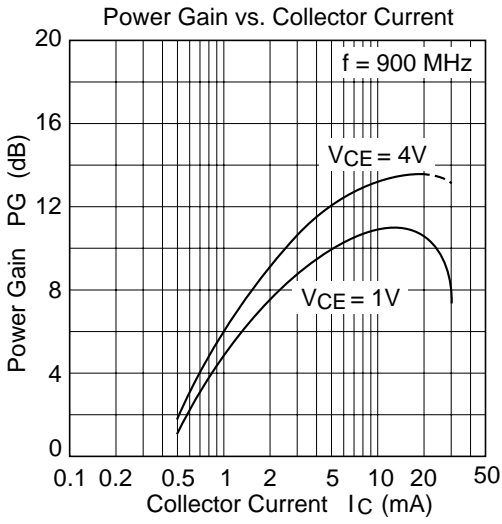


Gain Bandwidth Product vs. Collector Current

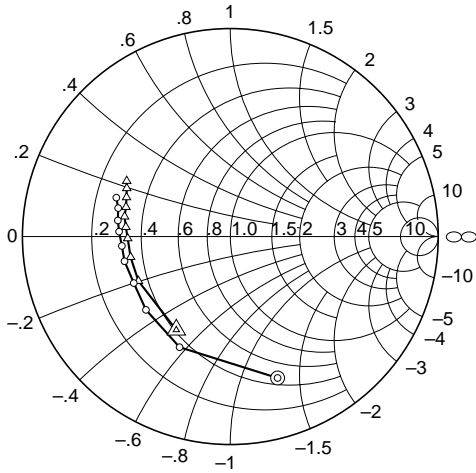


Collector Output Capacitance vs. Collector to Base Voltage





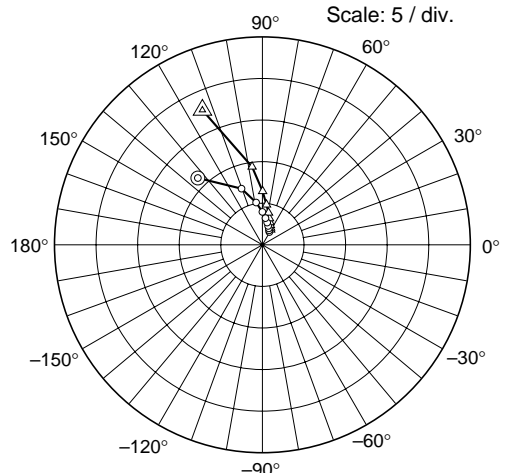
S11 Parameter vs. Frequency



Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

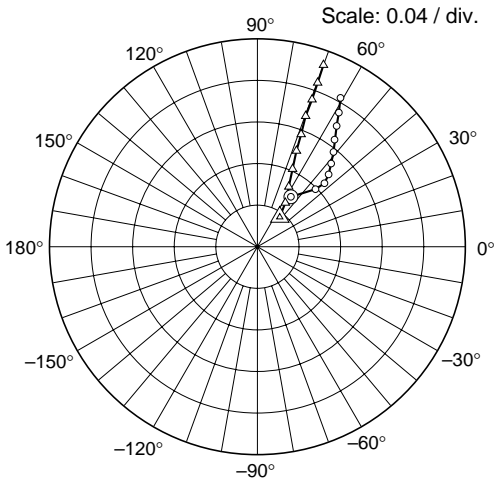
S21 Parameter vs. Frequency



Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

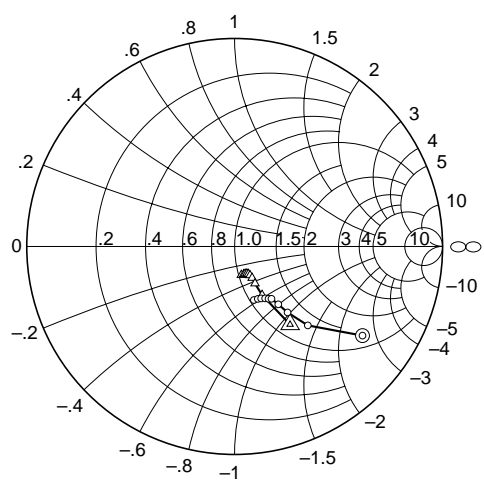
S12 Parameter vs. Frequency



Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

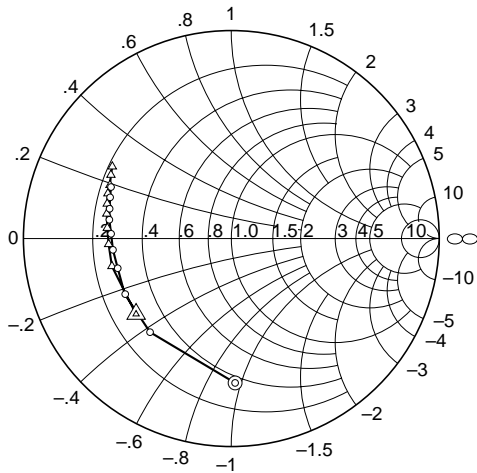
S22 Parameter vs. Frequency



Condition: $V_{CE} = 4\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

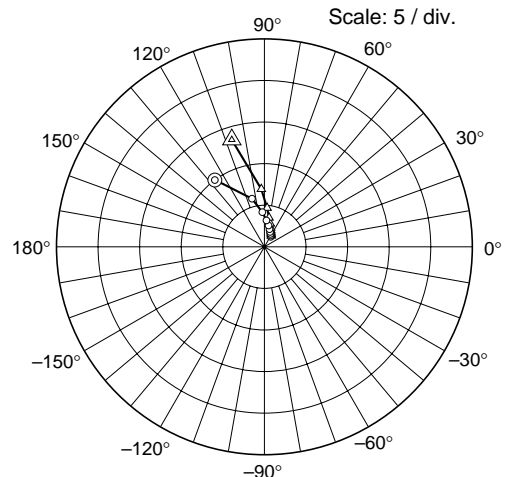
S11 Parameter vs. Frequency



Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

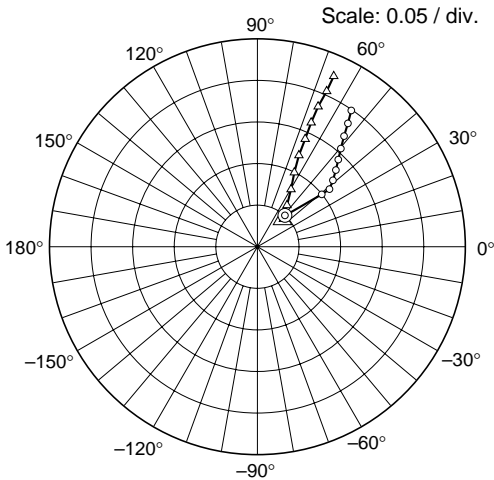
S21 Parameter vs. Frequency



Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

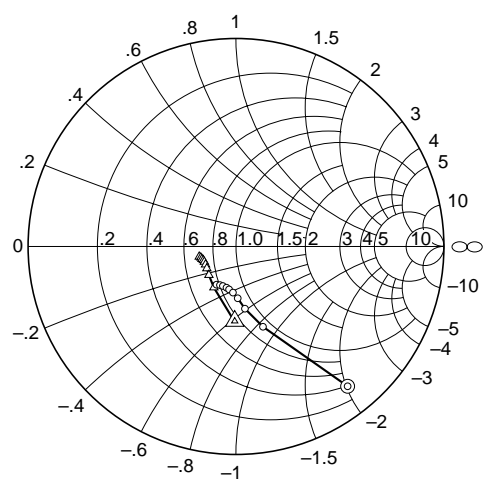
S12 Parameter vs. Frequency



Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

S22 Parameter vs. Frequency

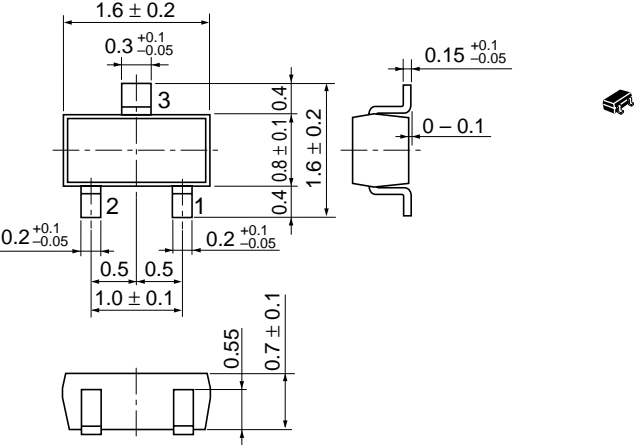


Condition: $V_{CE} = 1\text{ V}$, $Z_o = 50\ \Omega$
200 to 2000 MHz (200 MHz step)

○ — ○ ($I_C = 5\text{ mA}$)
△ — △ ($I_C = 20\text{ mA}$)

Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	SMPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.003 g

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HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
 Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
 Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
 (America) Inc.
 179 East Tasman Drive,
 San Jose, CA 95134
 Tel: <1> (408) 433-1990
 Fax: <1> (408) 433-0223

Hitachi Europe GmbH
 Electronic Components Group
 Dornacher Straße 3
 D-85622 Feldkirchen, Munich
 Germany
 Tel: <49> (89) 9 9180-0
 Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
 Electronic Components Group.
 Whitebrook Park
 Lower Cookham Road
 Maidenhead
 Berkshire SL6 8YA, United Kingdom
 Tel: <44> (1628) 585000
 Fax: <44> (1628) 585160

Hitachi Asia Ltd.
 Hitachi Tower
 16 Collyer Quay #20-00,
 Singapore 049318
 Tel : <65>-538-6533/538-8577
 Fax : <65>-538-6933/538-3877
 URL : <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
 (Taipei Branch Office)
 4/F, No. 167, Tun Hwa North Road,
 Hung-Kuo Building,
 Taipei (105), Taiwan
 Tel : <886>-(2)-2718-3666
 Fax : <886>-(2)-2718-8180
 Telex : 23222 HAS-TP
 URL : <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
 Group III (Electronic Components)
 7/F., North Tower,
 World Finance Centre,
 Harbour City, Canton Road
 Tsim Sha Tsui, Kowloon,
 Hong Kong
 Tel : <852>-(2)-735-9218
 Fax : <852>-(2)-730-0281
 URL : <http://www.hitachi.com.hk>

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